THE DATASHEET OF

MBR1070CT

MBR1070CT - MBR10100CT

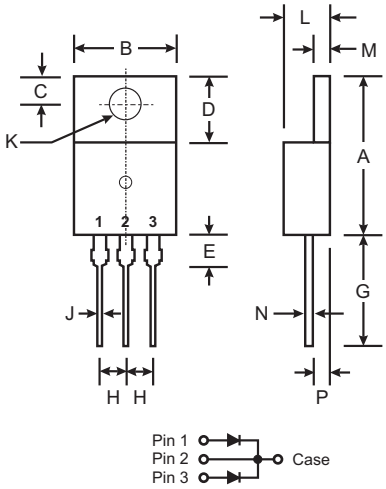
10A HIGH VOLTAGE SCHOTTKY BARRIER RECTIFIER

Features

- Schottky Barrier Chip
- Guard Ring Die Construction for Transient Protection
- Low Power Loss, High Efficiency
- High Surge Capability
- High Current Capability and Low Forward Voltage Drop
- For Use in Low Voltage, High Frequency Inverters, Free Wheeling, and Polarity Protection Applications
- **Lead Free Finish, RoHS Compliant (Note 3)**

Mechanical Data

- Case: TO-220AB
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Polarity: As Marked on Body
- Terminals: Finish – Bright Tin. Solderable per MIL-STD-202, Method 208
- Mounting Position: Any
- Marking: Type Number
- Weight: 2.24 grams (approx)



TO-220AB		
Dim	**Min**	**Max**
A	14.48	15.75
B	10.00	10.40
C	2.54	3.43
D	5.90	6.40
E	2.80	3.93
G	12.70	14.27
H	2.40	2.70
J	0.69	0.93
K	3.54	3.78
L	4.07	4.82
M	1.15	1.39
N	0.30	0.50
P	2.04	2.79
All Dimensions in mm		

Maximum Ratings and Electrical Characteristics @ T_A = 25°C unless otherwise specified

Single phase, half wave, 60Hz, resistive or inductive load.
For capacitive load, derate current by 20%.

Characteristic	Symbol	MBR 1070CT	MBR 1080CT	MBR 1090CT	MBR 10100CT	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	70	80	90	100	V
RMS Reverse Voltage	$V_{R(RMS)}$	49	56	63	70	V
Average Rectified Output Current (Note 1) @ T_C = 100°C	I_O	10				A
Non-Repetitive Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	120				A
Forward Voltage Drop @ I_F = 5.0A, T_C = 125°C @ I_F = 5.0A, T_C = 25°C @ I_F = 10A, T_C = 125°C @ I_F = 10A, T_C = 25°C	V_{FM}	0.75 0.85 0.85 0.95				V
Peak Reverse Current @ T_C = 25°C at Rated DC Blocking Voltage @ T_C = 125°C	I_{RM}	0.1 50				mA
Typical Junction Capacitance (Note 2)	C_j	300				pF
Typical Thermal Resistance Junction to Case (Note 1)	$R_{\theta JC}$	3.0				K/W
Voltage Rate of Change	dV/dt	10,000				V/μs
Operating and Storage Temperature Range	T_j, T_{STG}	-65 to +150				°C

Notes: 1. Thermal resistance junction to case mounted on heatsink.
2. Measured at 1.0MHz and applied reverse voltage of 4.0V DC.
3. RoHS revision 13.2.2003. Glass and High Temperature Solder Exemptions Applied, see *EU Directive Annex Notes 5 and 7.*

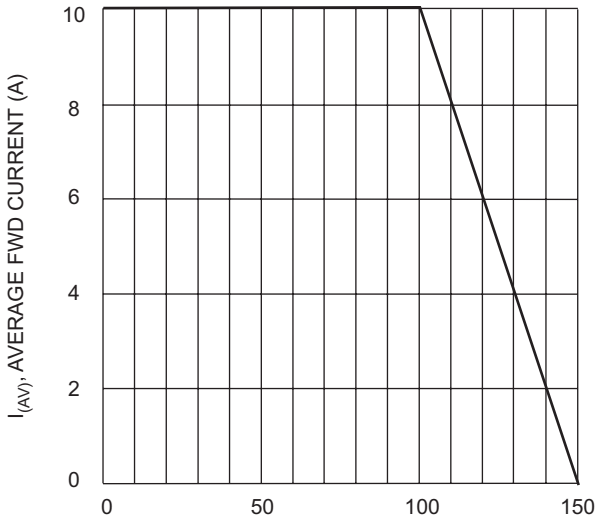


Fig. 1 Forward Current Derating Curve

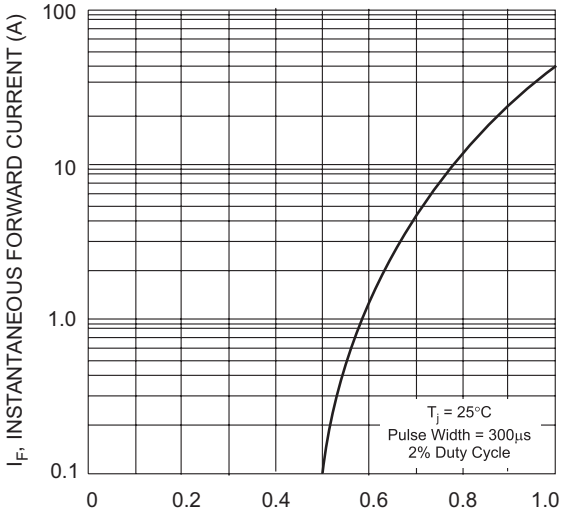


Fig. 2 Typical Forward Characteristics

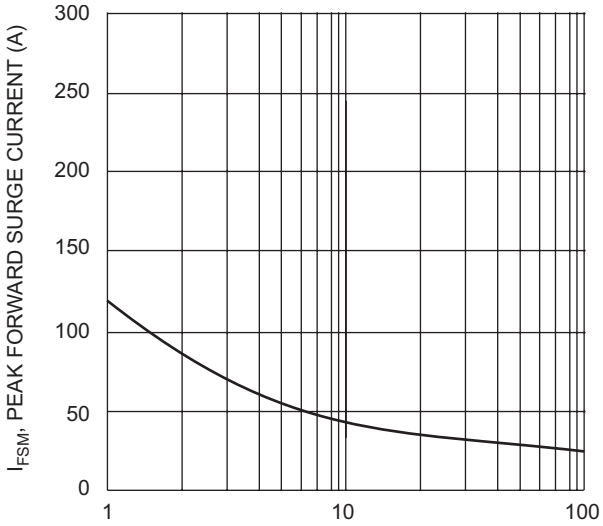


Fig. 3 Max Non-Repetitive Surge Current

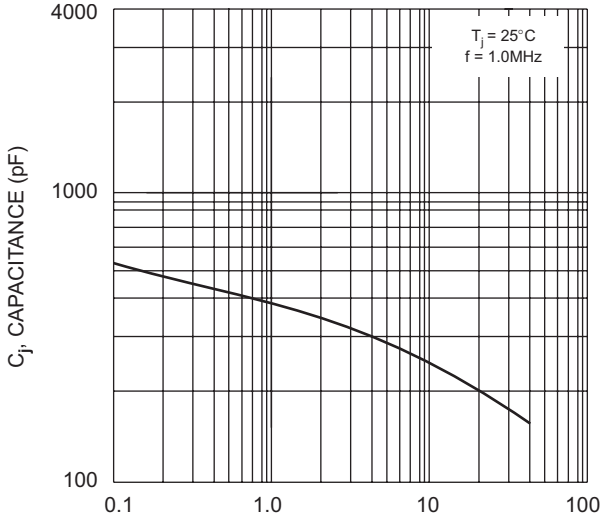


Fig. 4 Typical Junction Capacitance

Ordering Information (Note 4)

Device	Packaging	Shipping
MBR10xxCT*	TO-220AB	50/Tube

* xx = Device type, e.g. MBR1080CT

Notes: 4. For packaging details, visit our website at http://www.diodes.com/datasheets/ap02008.pdf.

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- Alternative Solution
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